



## 2N2327 thur 2N2329

### SILICON THYRISTORS

All-diffused PNP thyristors designed for grating operation in mA/ $\mu$ A signal or detection circuits  
 Compliance to RoHS.

#### MAXIMUM RATINGS (\*)

$T_J=125^{\circ}\text{C}$  unless otherwise noted,  $R_{GK}=1000\Omega$

Symbol	Ratings	2N2327	2N2328	2N2329	Unit
$V_{RSM(REP)}$	Peak reverse blocking voltage (1)	250	300	400	V
$V_{RSM(NON-REP)}$	Non-repetitive peak blocking reverse voltage ( $t<5.0$ ms)	350	400	500	V
$I_{T(RMS)}$	Forward Current RMS (all conduction angles)	1.6			A
$I_{TSM}$	Peak Surge Current (One-Half Cycle, 60Hz) No Repetition Until Thermal Equilibrium is Restored.	15			A
$P_{GM}$	Peak Gate Power – Forward	0.1			W
$P_{G(AV)}$	Average Gate Power - Forward	0.01			W
$I_{GM}$	Peak Gate Current – Forward	0.1			A
$V_{GFM}$	Peak Gate Voltage - Forward	6.0			V
$V_{GRM}$	Peak Gate Voltage - Reverse	6.0			V
$T_J$	Operating Junction Temperature Range	-65 to +125			°C
$T_{STG}$	Storage Temperature Range	-65 to +150			

## 2N2327 thur 2N2329

### ELECTRICAL CHARACTERISTICS (\*)

T<sub>J</sub>=25°C unless otherwise noted, R<sub>GK</sub>=1000Ω

Symbol	Ratings	2N2327	2N2328	2N2329	Unit
V <sub>DRM</sub>	Peak Forward Blocking Voltage (1) Min :	250	300	400	V
I <sub>RRM</sub>	Peak Reverse Blocking Current (Rated V <sub>DRM</sub> , T <sub>J</sub> =125°C)	Max : 100			μA
I <sub>DRM</sub>	Peak Forward Blocking Current (Rated V <sub>DRM</sub> , T <sub>J</sub> =125°C)	Max : 100			μA
V <sub>T</sub>	Forward « on » Voltage I <sub>T</sub> =1.0 A Peak	Max : 1.5			V
	I <sub>T</sub> =1.0 A Peak T <sub>C</sub> =85°C	Max : 2.0			
I <sub>GT</sub>	Gate Trigger Current (2) Anode Voltage=6.0 Vdc, R <sub>L</sub> =100Ω	Max : 200			μA
	Anode Voltage=6.0 Vdc, R <sub>L</sub> =100Ω T <sub>C</sub> =-65°C	Max : 350			
V <sub>GT</sub>	Gate Trigger Voltage Anode Voltage=6.0 V, R <sub>L</sub> =100Ω	Max : 0.8			V
	Anode Voltage=6.0 V, R <sub>L</sub> =100Ω T <sub>C</sub> =-65°C	Max : 1.0			
	V <sub>DRM</sub> = Rated, R <sub>L</sub> =100Ω T <sub>J</sub> =125°C	Min : 0.1			
I <sub>H</sub>	Holding Current Anode Voltage=6.0 V	Max : 2.0			mA
	Anode Voltage=6.0 V T <sub>C</sub> =-65°C	Max : 3.0			
	Anode Voltage=6.0 V T <sub>C</sub> =125°C	Min : 0.15			

(\*) JEDEC Registered Values

(1) V<sub>RSM</sub> and V<sub>DRM</sub> can be applied for all types on a continuous dc basis without incurring damage.

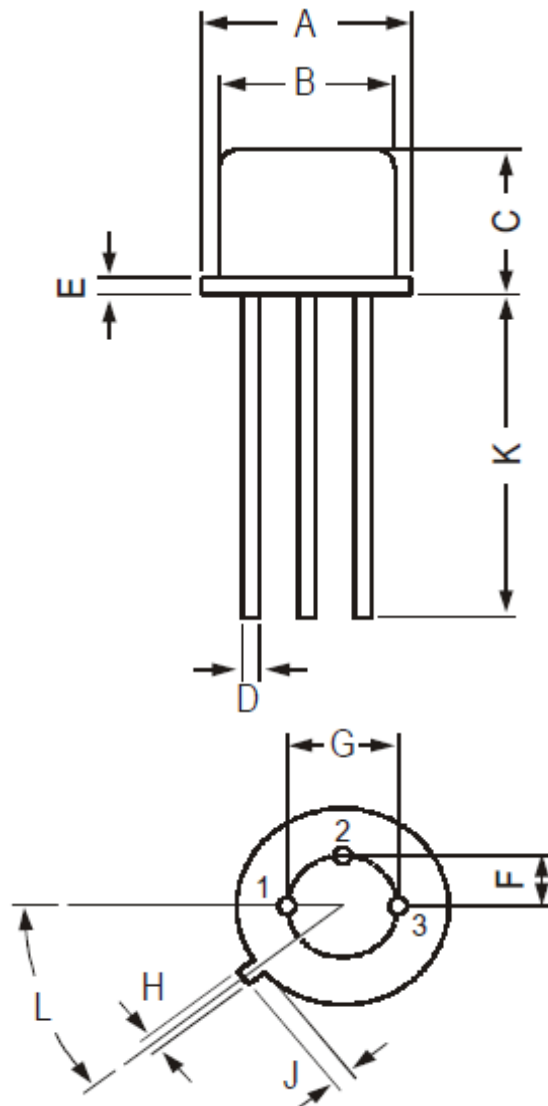
(2) R<sub>GK</sub> current is not included in measurement.

## 2N2327 thur 2N2329

### MECHANICAL DATA CASE TO-39

DIMENSIONS (mm)		
	min	max
A	8.50	9.39
B	7.74	8.50
C	6.09	6.60
D	0.40	0.53
E	-	0.88
F	2.41	2.66
G	4.82	5.33
H	0.71	0.86
J	0.73	1.02
K	12.70	-
L	42°	48°

Pin 1 :	kathode
Pin 2 :	Gate
Pin 3 :	Anode
Case :	anode



Revised October 2012

Information furnished is believed to be accurate and reliable. However, Comset Semiconductors assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. Data are subject to change without notice. Comset Semiconductors makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does Comset Semiconductors assume any liability arising out of the application or use of any product and specifically disclaims any and all liability, including without limitation consequential or incidental damages. Comset Semiconductors' products are not authorized for use as critical components in life support devices or systems.